

PRELIMINARY
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Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M63836FP/KP

8-UNIT 500mA DARLINGTON TRANSISTOR-ARRAY WITH CLAMP DIODE

DESCRIPTION

The M63836FP/KP 8-channel sinkdriver, consists of 8 PNP and 16 NPN transistors connected to from eight high current gain driver pairs.

FEATURES

- High breakdown voltage ($BV_{CEO} \geq 50V$)
 - High-current driving ($I_C(max) = 500mA$)
 - 3V micro computer compatible input
 - “L” active level input
 - With input diode
 - With clamping diodes
 - Wide operating temperature range ($T_a = -40$ to $+85^\circ C$)

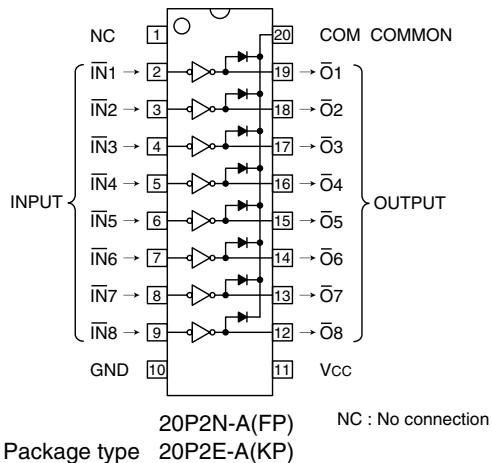
APPLICATION

Output for 3 voltage microcomputer series and interface with high voltage system. Relay and small printer driver, LED, or incandescent display digit driver.

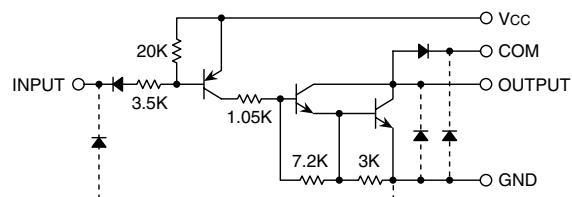
FUNCTION

The M63836FP/KP is transistor-array of high active level eight units type which can do direct drive of 3 voltage micro-computer series. A resistor of $3.5\text{k}\Omega$ is connected between the input and the base of PNP transistors. A clamp diode for inductive load transient suppression is connected for the output pin (collector) and COM pin. The input diode is intended to prevent the flow of current from the input to the Vcc. without this diode, the current flows from "H" input to the Vcc and the "L" input circuit is activated, in such a case where one of the inputs of the 8 circuit is "H" and the other are "L" to save power consumption. The diode is inserted to prevent such mis-operation. The outputs are capable of driving 500mA and are rated for operation with output voltage up to 50V.

PIN CONFIGURATION



CIRCUIT DIAGRAM



The eight circuits share the Vcc, COM and GND

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : Ω

ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, $T_a = -40 \sim +85^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage		7	V
V _{CEO}	Collector-emitter voltage	Output, H	-0.5 ~ +50	V
I _C	Collector current	Current per circuit output, L	500	mA
V _I	Input voltage		-0.5 ~ V _{CC}	V
I _F	Clamping diode forward current		500	mA
V _R	Clamping diode reverse voltage		50	V
P _d	Power dissipation	T _a = 25°C, when mounted on board	1.10(FP)/0.68(KP)	W
T _{opr}	Operating temperature		-40 ~ +85	°C
T _{stg}	Storage temperature		-55 ~ +125	°C

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RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, $T_a = -40 \sim +85^\circ\text{C}$)

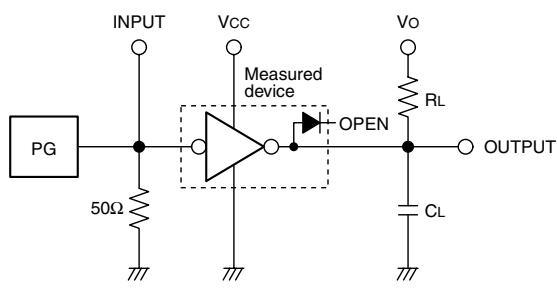
Symbol	Parameter	Limits			Unit
		min	typ	max	
V _{CC}	Supply voltage	2.7	3.0	3.6	V
I _C	Collector current (Current per 1 circuit when 8 circuits are coming on simultaneously)	Duty Cycle FP : no more than 4% KP : no more than 2%	0	—	400
		Duty Cycle FP : no more than 15% KP : no more than 6%	0	—	200
V _{IH}	"H" input voltage	V _{CC} -0.5	—	V _{CC}	V
V _{IL}	"L" input voltage	0	—	V _{CC} -2.2	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, $T_a = -40 \sim +85^\circ\text{C}$)

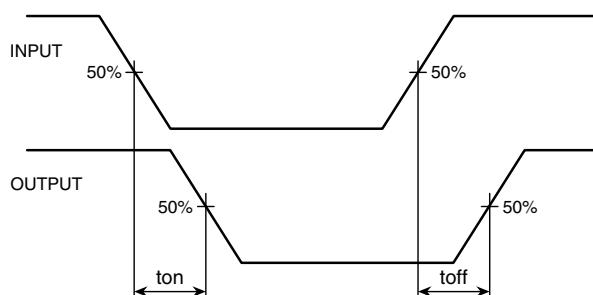
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _{CEO} = 100μA	50	—	—	V
V _{CESAT}	Collector-emitter saturation voltage	V _{CC} = 2.7V, V _I = 0.5V, I _C = 400mA	—	1.15	2.4	V
		V _{CC} = 2.7V, V _I = 0.5V, I _C = 200mA	—	0.93	1.6	
I _I	Input current	V _I = V _{CC} -2.2V	—	-220	-600	μA
V _F	Clamping diode forward voltage	I _F = 400mA	—	1.4	2.4	V
I _R	Clamping diode reverse current	V _R = 50V	—	0.1	100	μA
I _{CC}	Supply current (AN only Input)	V _{CC} = 3.6V, V _I = 0.5V	—	2.6	4.0	mA
h _{FE}	DC amplification factor	V _{CC} = 2.7V, V _{CES} = 2V, I _C = 0.35A, T _a = 25°C	2000	10000	—	—

* : Typical values are at $T_a = 25^\circ\text{C}$ **SWITCHING CHARACTERISTICS** (Unless otherwise noted, $T_a = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
t _{on}	Turn-on time	CL = 15pF (note 1)	—	120	—	ns
t _{off}	Turn-off time	CL = 15pF (note 1)	—	4500	—	ns

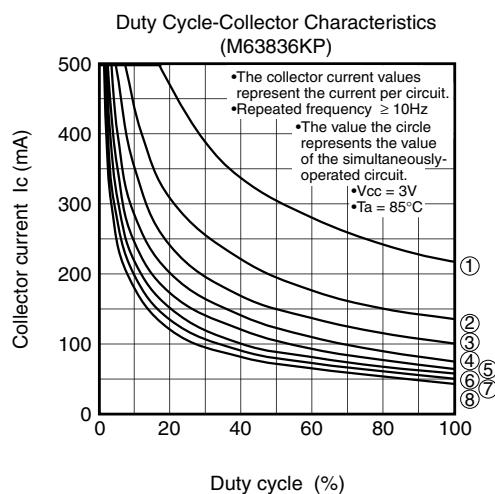
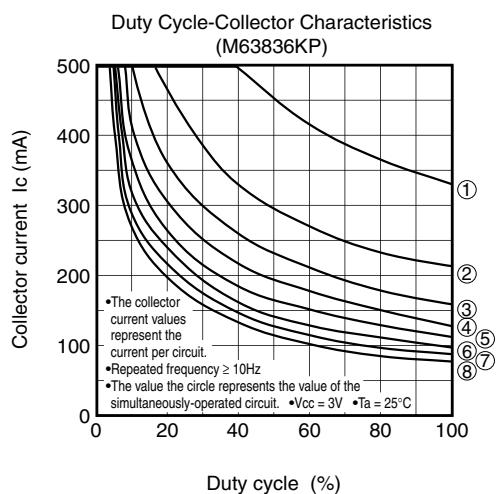
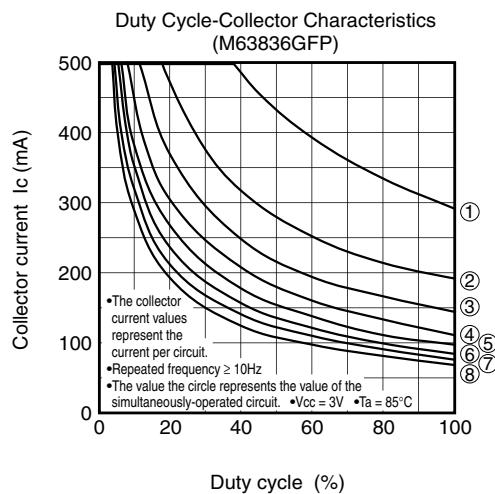
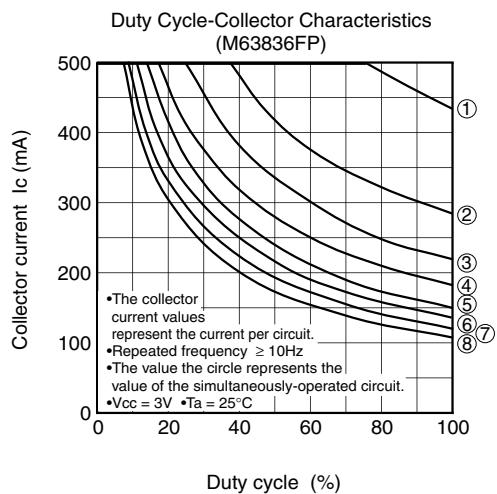
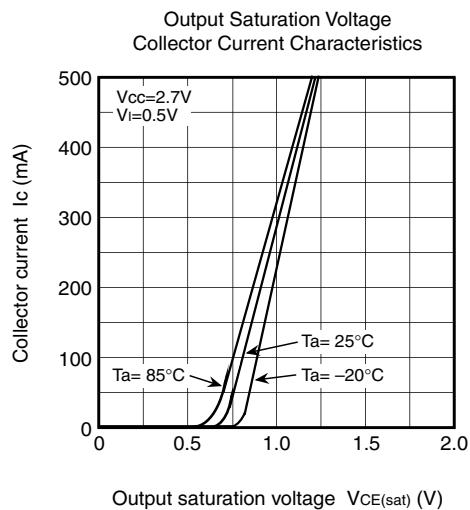
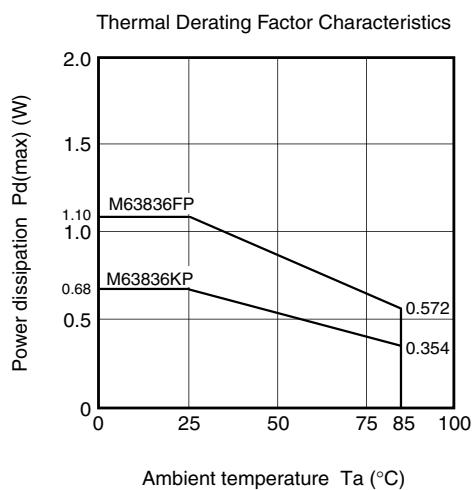
NOTE 1 TEST CIRCUIT

- (1)Pulse generator (PG) characteristics : PRR=1kHz,
tw = 10μs, tr = 6ns, tf = 6ns, Zo = 50Ω
Vi = 0.5 ~ 2.7V
- (2)Input-output conditions : RL = 30Ω, Vo = 10V, Vcc = 2.7V
- (3)Electrostatic capacity CL includes floating capacitance
at connections and input capacitance at probes

TIMING DIAGRAM

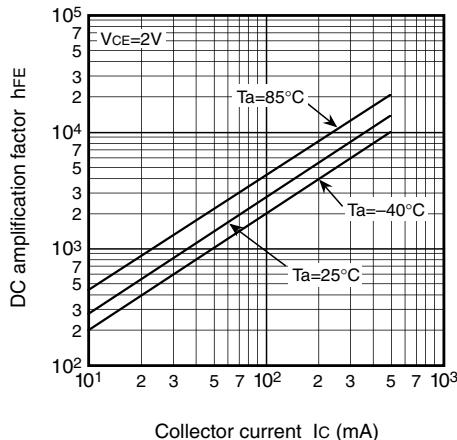
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TYPICAL CHARACTERISTICS

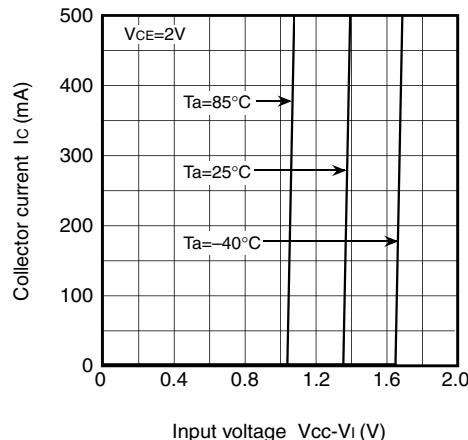


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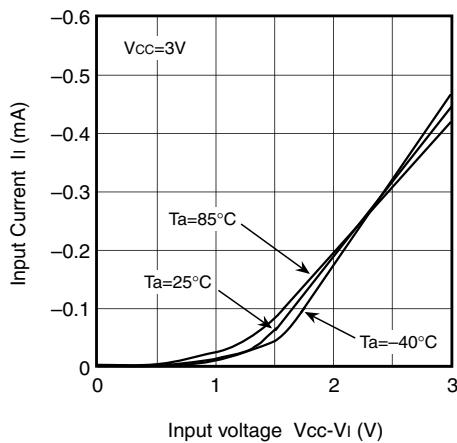
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DC Amplification Factor
Collector Current Characteristics

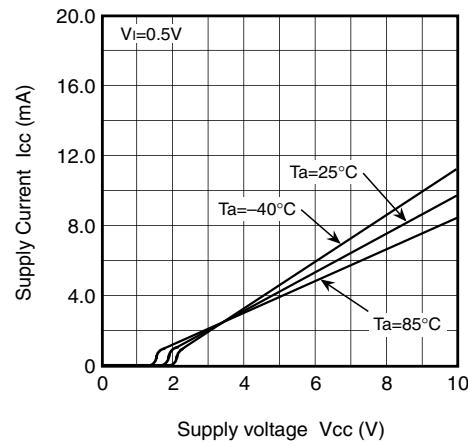
Output Current Characteristics



Input Characteristics



Driver Supply Characteristics



Clamping Diode Characteristics

